

**Pin Definition:**

1. Gate
2. Drain
3. Source

**PRODUCT SUMMARY**

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
75	8 @ V <sub>GS</sub> =10V	80

**Features**

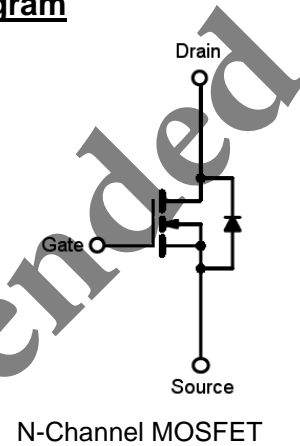
- Advanced Trench Technology
- Low R<sub>DS(ON)</sub> 8mΩ (Max.)
- Low gate charge typical @ 91.5nC (Typ.)
- Low Crss typical @ 203pF (Typ.)

**Ordering Information**

Part No.	Package	Packing
TSM80N08CZ C0G	TO-220	50pcs / Tube

**Note:** "G" denotes for Halogen Free

**Block Diagram**



**Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	75	V	
Gate-Source Voltage	V <sub>GS</sub>	±25	V	
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> =25°C	80	A
		T <sub>C</sub> =70°C	60	
		T <sub>A</sub> =25°C	12	
		T <sub>A</sub> =70°C	9	
Drain Current-Pulsed Note 1	I <sub>DM</sub>	320	A	
Avalanche Current, L=0.3mH	I <sub>AS</sub>	35	A	
Avalanche Energy, L=0.3mH	E <sub>AS</sub>	183	mJ	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> =25°C	113.6	W
		T <sub>C</sub> =70°C	72.7	
		T <sub>A</sub> =25°C	2	
		T <sub>A</sub> =70°C	1.3	
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C	
Operating Junction Temperature Range	T <sub>J</sub>	-55 to +150	°C	

\* Limited by maximum junction temperature

**Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	Rθ <sub>JC</sub>	1.1	°C/W
Thermal Resistance - Junction to Ambient	Rθ <sub>JA</sub>	62.5	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec

### Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$	75	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 40A$	$R_{DS(ON)}$	--	6	8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	$I_{DSS}$	--	--	1	μA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	$I_{GSS}$	--	--	±100	nA
<b>Dynamic</b>						
Total Gate Charge	$V_{DS} = 30V, I_D = 40A,$ $V_{GS} = 10V$	$Q_g$	--	91.5	--	nC
Gate-Source Charge		$Q_{gs}$	--	34	--	
Gate-Drain Charge		$Q_{gd}$	--	19.9	--	
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0MHz$	$C_{iss}$	--	3905	--	pF
Output Capacitance		$C_{oss}$	--	371	--	
Reverse Transfer Capacitance		$C_{rss}$	--	203	--	
<b>Switching</b>						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 30V,$ $I_D = 1A, R_G = 3.3\Omega$	$t_{d(on)}$	--	21.5	--	nS
Turn-On Rise Time		$t_r$	--	11	--	
Turn-Off Delay Time		$t_{d(off)}$	--	73	--	
Turn-Off Fall Time		$t_f$	--	66	--	
<b>Drain-Source Diode Characteristics and Maximum Rating</b>						
Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=20A$	$V_{SD}$	-	0.8	1.3	V
Reverse Recovery Time	$I_S = 40A, T_J = 25^\circ C$	$t_{fr}$		36		nS
Reverse Recovery Charge	$dI/dt = 100A/\mu s$	$Q_{fr}$		45		nC

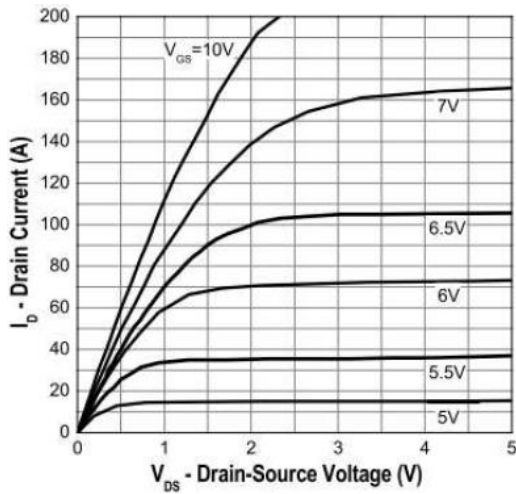
#### Notes:

1. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2.  $R\theta_{JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R\theta_{JC}$  is guaranteed by design while  $R\theta_{CA}$  is determined by the user's board design.  $R\theta_{JA}$  shown below for single device operation on FR-4 in still air

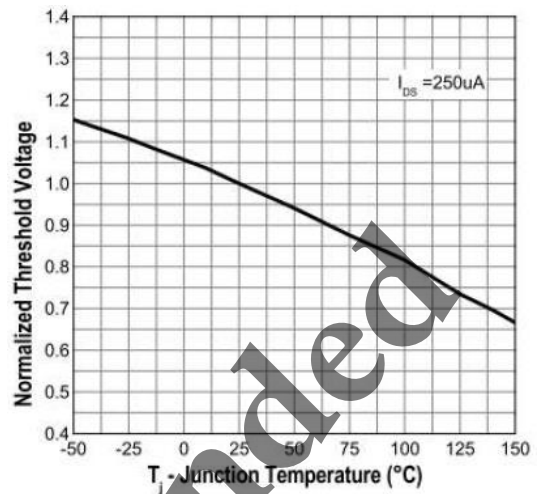


**Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

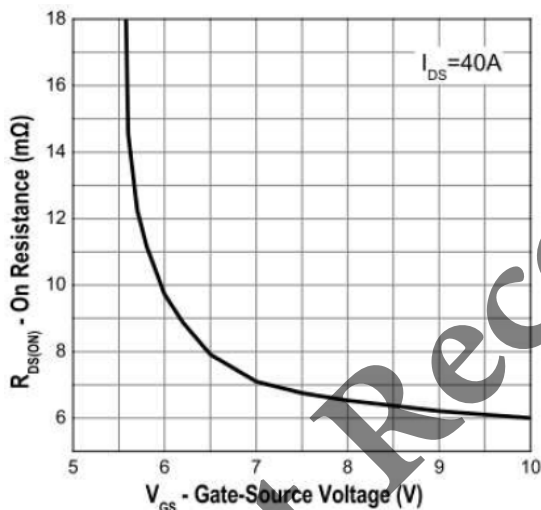
**Output Characteristics**



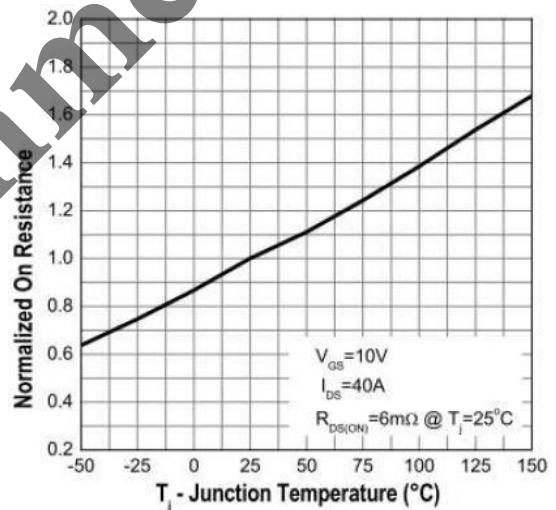
**Gate Threshold Voltage**



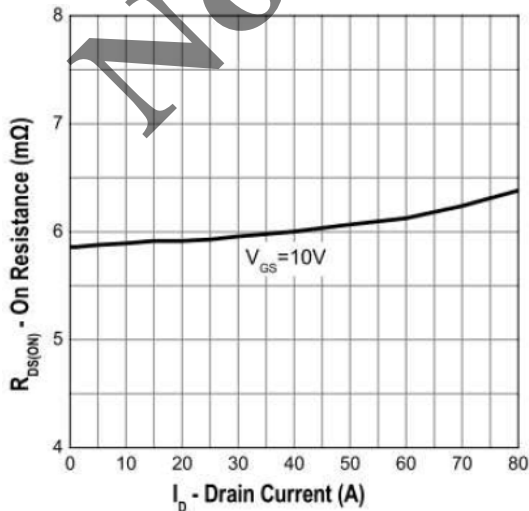
**Gate Source On Resistance**



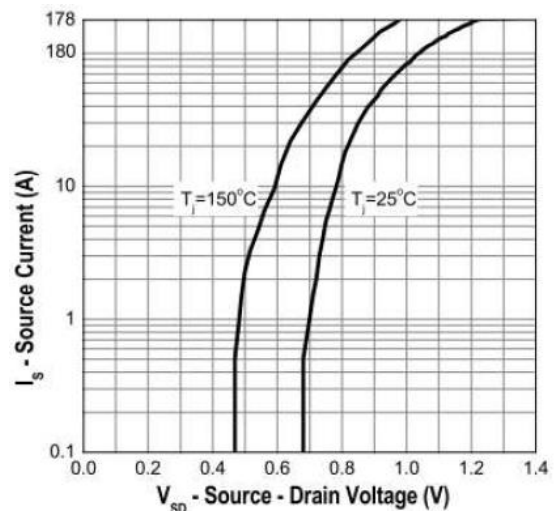
**Drain-Source On Resistance**



**Drain-Source On-Resistance**



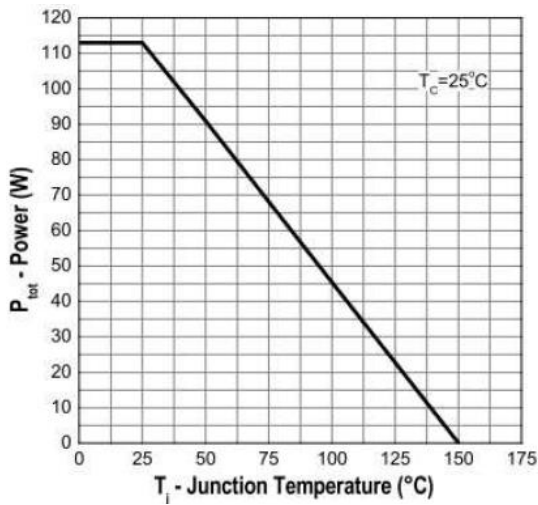
**Source-Drain Diode Forward Voltage**



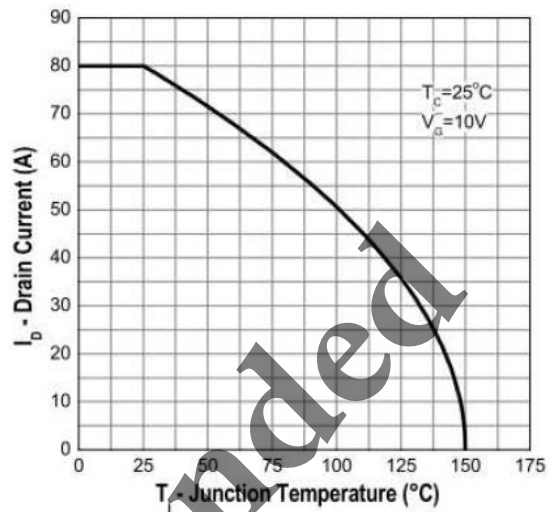


**Electrical Characteristics Curve** ( $T_a = 25^\circ\text{C}$ , unless otherwise noted)

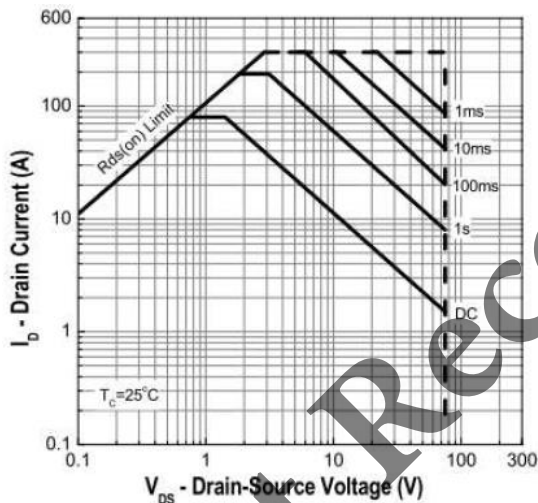
**Power Derating**



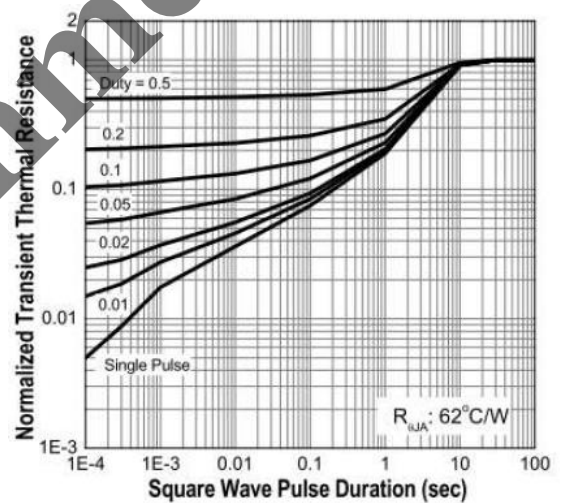
**Drain Current vs. Junction Temperature**



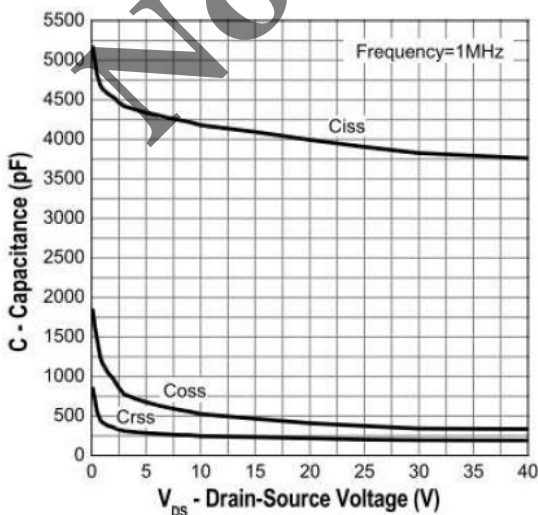
**Safe Operation Area**



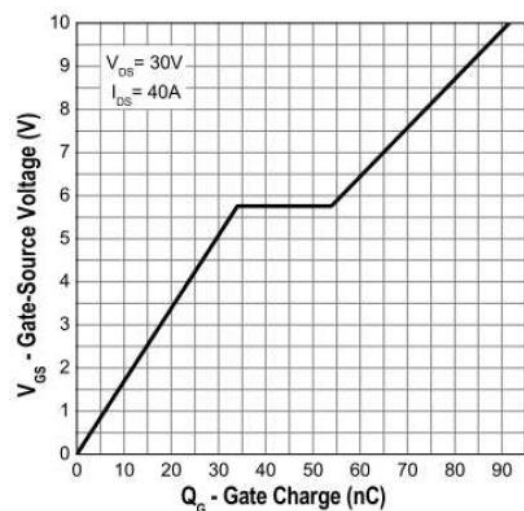
**Transient Thermal Impedance**



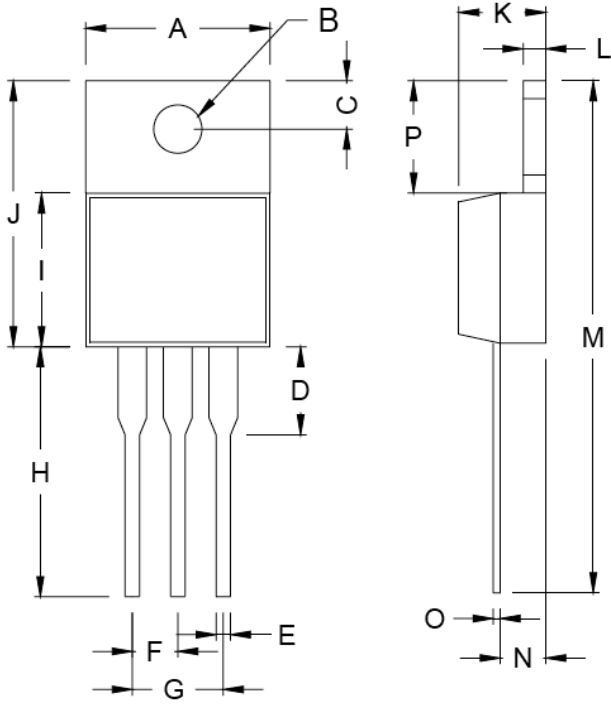
**Capacitance**



**Gate Charge**



**TO-220 Mechanical Drawing**



TO-220 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	10.000	10.500	0.394	0.413
B	3.740	3.910	0.147	0.154
C	2.440	2.940	0.096	0.116
D	-	6.350	-	0.250
E	0.381	1.106	0.015	0.040
F	2.345	2.715	0.092	0.058
G	4.690	5.430	0.092	0.107
H	12.700	14.732	0.500	0.581
J	14.224	16.510	0.560	0.650
K	3.556	4.826	0.140	0.190
L	0.508	1.397	0.020	0.055
M	27.700	29.620	1.060	1.230
N	2.032	2.921	0.080	0.115
O	0.255	0.610	0.010	0.024
P	5.842	6.858	0.230	0.270

Not Recommended

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